MIL-PRF-38534 CERTIFIED FACILITY

RAD HARD QUAD PRECISION RAIL TO RAIL CURRENT SENSE AMP

496RH

FEATURES:



- Manufactured using TECHNOLOGY RH6105 Dice
 Radiation Hardened to 100 Krad(Si) (Method 1019.7 Condition A)
- Low Dose Rate Hardened to 50 Krad(Si) (Method 1019.7 Condition D)
- Neutron Tested to $5X10^{11}$ n/cm² (Method 1017.2)
- Very Wide Input Common Mode Range

TTM Technologies.

- Extends 44V Above V- (Independent of V+)
- Extends -0.3V Below V-
- Wide Power Supply Range: 2.85V to 36V
- Input Offset Voltage: 400µV Maximum
- Gain Accuracy: 1% Max
- · Gain Configurable with External Resistors
- Operating Current: 195µA typ. per Amp
- Slew Rate: 2V/µs
- Sense Input Current When Powered Down: <1µA
- Full-Scale Output Current: 1mA Minimum
- Non-Rad Hard EDU's Available
- Available to DLA SMD 5962R16201

DESCRIPTION:



The MSK496RH is a radiation hardened quad precision micropower current sense amplifier with a very wide input common mode range. With Over-the-Top[®] Technology, the MSK496RH is capable of sensing in high side or low side applications. This combined with external gain setting, and common mode and power supply rejection in excess of 100dB, make the MSK496RH well suited for a variety of current sensing applications. The MSK496RH is hermetically sealed in a 16 pin flat pack, and is available with straight or gull wing lead form.



ABSOLUTE MAXIMUM RATINGS

Input Voltage (+IN, -IN to V-)	9.5V to 44V
Differential Input Voltage	44V
Total Supply Voltage from V	36V
Output Short Circuit Duration	Indefinite ④

(9)

TST	Storage Temperature Range (2)	65°C to +150°C
ILD	Leau Temperature Range	
	(10 Seconds)	300°C
ΤJ	Junction Temperature	150°C
Тс	Case Operating Temperature Range	
	MSK496KRH, HRH	55°C to +125°C
	MSK496RH	40°C to +85°C
	MSK496EDU 1	40°C to +85°C
	ESD Rating	Class 1B

ELECTRICAL SPECIFICATIONS

Parameter	Test Conditions (1)(10)		Group A	MSK 496KRH/HRH			MSK 496RH/EDU			Unite
Falameter			Subgroup	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Voltage Gain Error (1)	VSENSE = 25mV to 75mV		1	-1	0.1	1	-1	-	+1	%
			2, 3	-1.5	0.1	1.5	-	-	-	%
Voltage Gain Error	VSENSE = 25mV to 75mV		1, 2, 3	-4.25	-	+2.25	-4.25	-	+2.25	%
	Vs + = 0V	Post Irradiation	1	-4.5	-	+4.5	-4.5	-	+4.5	%
	Vsense = 25mV; Vs + = 12V		1	-0.4	-0.1	0.4	-0.4	-0.1	-0.4	mV
			2, 3	-0.9	-	0.9	-	-	-	mV
Input Onse Voltage (1)		Post Irradiation Condition A	1	-1.0	-	1.0	-1.0	-	1.0	mV
		Post Irradiation Condition D	1	-2.0	-	1.0	-2.0	-	1.0	mV
	VSENSE = 5mV; Vs + = 0V		1	-1	-0.3	1	-1	-0.3	1	mV
Input Offset Voltage (2)			2, 3	-1.6	-	1.6	-	-	-	mV
		Post Irradiation	1	-1.2	-	1.2	-1.2	-	1.2	mV
	VSENSE = 5mV; Vs + = 2.8V to 44V		4	100	120	-	100	120	-	dB
Input Common Mode Rejection Ratio			5, 6	95	-	-	-	-	-	dB
		Post Irradiation	4	90	-	-	90	-	-	dB
Power Supply Rejection Ratio	$1/251/25 = 5m^{1/2} + 2.95^{1/2} + 2.95^{1/2}$		4	98	120	-	98	120	-	dB
	$V_{SENSE} = 5111V, V + = 2.85V 10.56V$	5, 6	94	-	-	-	-	-	dB	
		Post Irradiation	4	90	-	-	90	-	-	dB
Input Current	Vsense = 0V; Vs + = 3V; Av = 25 Vsense = 0V; Vs + = 0V		1, 2, 3	-	18	30	-	18	30	μA
			-	-	-0.05	-	-	-0.05	-	μA
	Vsense = 0V; Vs + = 3V; Av = 25 Vsense = 0V; Vs + = 0V		1, 2, 3	-	0.35	0.8	-	0.35	0.8	μA
			-	-	0.1	-	-	0.1	-	μA
V+ Supply Current	Vsense = 0V; Vs + = 3V; V + = 36V		1, 2, 3	-	780	1800	-	780	1800	μA
Minimum Output Voltage	VSENSE = 0mV; Vs + = 44V; V + = 36V		1	-	-	45	-	-	45	mV
			2, 3	-	-	90	-	-	90	mV
Output High (Referred to V +)	VSENSE = 120m	V; Av = 100; Rout = 10K	1, 2, 3	-	1.3	1.7	-	1.3	1.7	V
-3dB Bandwidth (3)	VSENSE =	50mV; Av = 10V/V	-	-	100	-	-	100	-	kHz
Thermal Resistance (Each Amplifier) (2)) Junction to Case @ 125°C		-	-	7.3	9.6	-	7.3	9.6	°C/W

NOTES:

(1)Unless otherwise specified; V+ = 12V, V- = 0V, VS+ = 12V, RIN1 = RIN2 = 100Ω, ROUT = 5K(AV = 50), VSENSE = (VS+)-(VS-).

- Guaranteed by design but not tested.
- 2 3 4 5 6 7 Typical parameters are representative of device performance but are for reference only.
- A heat sink may be required to keep the junction temperature below absolute maximum ratings.
- Industrial grade devices shall be tested to subgroups 1 and 4 unless otherwise requested.
- Military grade devices ("H" and "K" suffix) shall be 100% tested to subgroups 1, 2, 3 and 4.
- Subgroup 5 and 6 testing available upon request.

(8) TA = +25°C Subgroup 1, 4

- 2, 5 TA = +125°C 3, 6 TA = -55°C
- (9) Continuous operation at or above absolute maximum ratings may adversely affect the device performance and/or life cycle.

(10) Pre and post irradiation limits at 25°C, up to 100 Krad(Si) TID (Condition A) and 50 Krad(Si) TID (Condition D), are identical unless otherwise specified.

(11) MSK496EDU does not use Rad Hard die, post irradiation specifications are not applicable.

(12) Internal solder reflow temperature is 180°C, do not exceed.

APPLICATION NOTES

PIN FUNCTIONS

-INx- The *-*IN pin is the negative input terminal of the sense amplifier. Voltages as high as 44V can be applied to the pin, relative to the negative supply pin V-.

+INx - The +IN pin is the positive input terminal of the sense amplifier. Voltages as high as 44V can be applied to the pin, relative to the negative supply pin V-.

 $V\!\!+$ - The V^+ pin is the positive power supply for all amplifiers. Operational currents are sourced from this pin independent of the voltages on the -IN and +IN pins.

V- - The V- pin is the negative power supply for all amplifiers. Connect to the negative supply voltage or circuit ground for single supply opperation.

VOUTx - The VOUT pin is the output of the amplifier. The voltage at the output is a function of both the input differential (VSENSE± VOS), and the voltage gain ROUT/RIN1, for RIN1= RIN2. (See typical application ckt for more detail)

VOUT = ROUT/RIN x (VSENSE ± VOS) Set RIN1 = RIN2 for best accuracy

CASE - Pins 6 and 14 provide an electrical connection to the device package only. These pins are isolated from the internal circuit. Tie to a low impedance source or system ground to minimize coupling between amplifiers.

SENSE RESISTOR

Choose a $R_{_{\text{SENSE}}}$ resistor value just large enough to cover the application dynamic range to minimize power dissipation losses. The low 100 μV typical offset voltage helps to maintain high resolution while minimizing power dissipation.

Kelvin connection of the input resistors to the sense resistor is recommended to minimize error in high current applications.





RADIATION TEST PERFORMANCE

Radiation performance curves have been generated for all radiation testing performed by MS Kennedy. These curves show performance trends throughout each test process and are located in the MSK196RH radiation test report. The complete radiation test report is available in the RAD HARD PRODUCTS section on the MSK website.

ADDITIONAL APPLICATION INFORMATION

For additional applications information, please reference Linear Technology Corporation's ${\rm I\!R}$ LT6105 data sheet.

HIGH VOLTAGE SENSING

For high voltage applications, the MSK496RH can be used with external MOSFETs. The MOSFETs protect the device from the full potential of the high voltage supply. The high voltage supply is the positive rail of the device, and the Zener voltage minus the VGS(on) potential of Q2 determines the negative voltage rail for the device; (V-)=(V+)-(VZ-VGS). The device can safely sense current from 0.3V below the negative rail up to 44V above it independent of high voltage supply, and deliver a ground referenced signal via Q1. The values in the application circuit are provided for reference. They may need to be adjusted based on specific application requirements.

HIGH VOLTAGE SIMPLE CURRENT MONITOR





MECHANICAL SPECIFICATIONS





The above example is a Class K screened device with straight leads. For Non-Rad Hard engineering units, order MSK496EDU.

<u>NOTE:</u> See DLA SMD 5962R16201 for DLA part number options.

MECHANICAL SPECIFICATIONS CONT



G = GULL WING

BLANK = INDUSTRIAL; H = MIL-PRF-38534 CLASS H;

K = MIL-PRF-38534 CLASS K

——GENERAL PART NUMBER

The above example is a Class K screened device with gull wing lead form. For Non-Rad Hard engineering units, order MSK496EDUG.

<u>NOTE</u>: See DLA SMD 5962R16201 for DLA part number options.

REVISION HISTORY

REV	STATUS	DATE	DESCRIPTION
F	Released	04/14	Add low dose rate test bullet and adjust VOS1 post rad specifications
G	Released	05/14	Revise V+ supply current and shutdown input current typical values
Н	Released	06/14	Add ESD rating
I	Released	10/14	Revise R0JC
J	Released	10/21	Switch input terminals in high voltage circuit & remove MIL-PRF-38535
K	Released	09/23	Change Line Regulation Calculation

TTM Technologies

www.ttm.com

The information contained herein is believed to be accurate at the time of printing. TTM Technologies reserves the right to make changes to its products or specifications without notice, however and assumes no liability for the use of its products. Please visit our website for the most recent revision of this data sheet.